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## **Supporting Information**

## Discovery of a Ce<sup>3+</sup>-Activated Red Nitride Phosphor for High-Brightness Solid-State Lighting

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Figure S1. Rietveld refinement of observed HP-CaSiN<sub>2</sub> XRD pattern on the basis of AP-CaSiN<sub>2</sub> structure.



Figure S2. Excitation and emission spectra of none-doped HP-CaSiN<sub>2</sub>.



**Figure S3.** XRD patterns for HP-Ca<sub>(1-x)</sub>SiN<sub>2</sub>: $xCe^{3+}$  (x = 0-5.0%).



**Figure S4.** (a) The excitation ( $\lambda_{em}$  = 610 nm), (b) emission spectra ( $\lambda_{ex}$  = 450 nm) and emission intensity of HP-Ca<sub>(1-x)</sub>SiN<sub>2</sub>:xCe<sup>3+</sup>.



Figure S5. Temperature-dependent normalized integrated PL intensities of HP-  $Ca_{0.98}SiN_2:0.02Ce^{3+}$ .



Figure S6. Temperature-dependent quantum efficiency of HP-Ca<sub>0.98</sub>SiN<sub>2</sub>:0.02Ce<sup>3+</sup>.



**Figure S7.** Temperature-dependent decay curves of HP-Ca $_{0.98}$ SiN<sub>2</sub>:0.02Ce<sup>3+</sup> monitored at 610 nm, excited at 450 nm.



**Figure S8.** Luminescence spectra of the fabricated white LED driven by current increasing from 100 to 1000 mA.

**Table S1.** The space group, band gap, average bond length  $(R_{av})$  and distortion index (D) of

Nitride	Space group	Band gap (PBE) <sup>a)</sup>	$R_{av}^{b)}$	distortion index (D) <sup>b)</sup>
SrSi <sub>6</sub> N <sub>8</sub>	Imm2	3.21 <sup>1</sup>	3.028	0.048
BaSi <sub>6</sub> N <sub>8</sub>	lmm2	3.25 <sup>1</sup>	3.062	0.040
$SrSi_7N_{10}$	Рс	4.28 <sup>1</sup>	3.268	0.082
BaSi <sub>7</sub> N <sub>10</sub>	Рс	4.11 <sup>1</sup>	3.247	0.043
$Ca_2Si_5N_8$	Сс	3.65 <sup>1</sup>	2.638	0.082
$Sr_2Si_5N_8$	Pmn2 <sub>1</sub>	3.20 <sup>1</sup>	2.866	0.068
$Ba_2Si_5N_8$	Pmn2 <sub>1</sub>	2.88 <sup>1</sup>	2.917	0.046
$LaSi_3N_5$	P2 <sub>1</sub> 2 <sub>1</sub> 2 <sub>1</sub>	3.19 <sup>1</sup>	2.700	0.049
$La_3Si_6N_{11}$	P4bm	2.97 <sup>1</sup>	2.647	0.001
ZnSiN <sub>2</sub>	Pna2 <sub>1</sub>	4.83 <sup>2</sup>	2.109	0.010
$MgSiN_2$	Pna2 <sub>1</sub>	3.97 <sup>1</sup>	2.090	0.011
Cubic-CaSiN <sub>2</sub>	E2m	4.50 <sup>3</sup>	2 /01	0.070
(Ca <sub>16</sub> Si <sub>17</sub> N <sub>34</sub> )	FJIII	(optical band gap)	2.401	0.079
AP-CaSiN <sub>2</sub>				
(ambient-	Pbca	3.44	2.506	0.046
pressure phase)				
HP-CaSiN <sub>2</sub>				
(high-pressure	Pbca	3.44	2.570	0.086
phase)				
SrSiN <sub>2</sub>	P21/c	2.97 <sup>1</sup>	2.843	0.069
$BaSiN_2$	Стса	2.92 <sup>1</sup>	2.986	0.061
$La_5Si_3N_9$	Стса	1.97 <sup>1</sup>	2.553	0.074
$Ca_5Si_2N_6$	C2/c	2.46 <sup>1</sup>	2.447	0.023
$Ba_5Si_2N_6$	P212121	1.40 <sup>1</sup>	2.977	0.073
Ca <sub>4</sub> SiN <sub>4</sub>	P21/c	1.45 <sup>1</sup>	2.454	0.034
		4		

potential nitridosilicate candidates.

	14 /	4.90 <sup>4</sup>	2 0 6 2	0.040
Srivig <sub>3</sub> SiN <sub>4</sub>	14 <sub>1</sub> /a	(optical band gap)	2.863	0.049
$CaMg_3SiN_4$	14 <sub>1</sub> /a	<b>2.60</b> <sup>5</sup>	2.733	0.052
BaMg3SiN4	Р	4.00 <sup>4</sup> (optical band gap)	2.953	0.015
$Ca_3Li_4Si_2N_6$	C2/m	2.29 <sup>1</sup>	2.580	0.045
$Sr_3Li_4Si_2N_6$	C2/m	unknown	2.706	0.022
SrAlSi <sub>4</sub> N <sub>7</sub>	Pna2 <sub>1</sub>	3.58 <sup>1</sup>	2.713	0.054
$Ba_2AlSi_5N_9$	P1	unknown	2.955	0.030
SrYSi <sub>4</sub> N <sub>7</sub>	P6₃mc	2.74 <sup>1</sup>	3.012	0.015
CaLi <sub>2</sub> Si <sub>2</sub> N <sub>4</sub>	Ра	3.46 <sup>6</sup>	2.499	0.004
$SrLi_2Si_2N_4$	Ра	3.44 <sup>1</sup>	2.689	0.001
CaAlSiN <sub>3</sub>	Cmc21	3.36 <sup>7</sup>	2.470	0.053
$Ca_5Al_2Si_2N_8$	Pbcn	2.79 <sup>1</sup>	2.526	0.033
Sr <sub>8</sub> Mg <sub>7</sub> Si <sub>9</sub> N <sub>22</sub>	C2/m	2.90 <sup>8</sup>	2.764	0.035
$Ca_3LiSi_2N_5$	C2/c	<b>2.44</b> <sup>1</sup>	2.511	0.039
$La_{17}Al_4Si_9N_{33}$	F3m	1.88 <sup>1</sup>	2.578	0.011
$Li_5La_5Si_4N_{12}$	Pb2	unknown	2.580	0.032
$Sr_4Li_2Si_2N_6$	Ра	2.20 <sup>1</sup>	2.671	0.029
$Ca_2Ba_3Si_2N_6$	C2/c	1.55 <sup>1</sup>	2.513	0.040
$MgBa_4Si_2N_6$	Fddd	1.59 <sup>1</sup>	2.845	0.047
$Li_2Ca_2Mg_2Si_2N_6$	C2/m	4.26 <sup>9</sup> (optical band gap)	2.588	0.041
Li <sub>2</sub> Ca <sub>3</sub> MgSi <sub>2</sub> N <sub>6</sub>	C2/m	unknown	2.513	0.038
Li <sub>4</sub> Ca <sub>2</sub> MgSi <sub>2</sub> N <sub>6</sub>	C2/m	unknown	2.482	0.015
$BaLi_2Al_2Si_2N_6$	P4/ncc	4.60 <sup>10</sup> (optical band gap)	3.017	0.027
KLaSi(CN <sub>2</sub> ) <sub>4</sub>	P21221	unknown	2.609	0.018
RbLaSi(CN <sub>2</sub> ) <sub>4</sub>	1	unknown	2.607	0.019

<sup>a)</sup> (The optical band gap is multiplied by 67% to convert to an approximate PBE band gap.); <sup>b)</sup> (The values of  $R_{av}$  and D are collected from ICSD; For multi-lattice structures, the smallest  $R_{av}$  and corresponding D values are selected.)

Table S2. Sele	ected bond	lengths of H	IP-CaSiN₂:Ce <sup>3+</sup> .
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Atom	Distance (Å)	Atom	Distance (Å)
(Ca1/Ce1) – N1	2.371(34)	(Ca2/Ce2) – N1	2.546(26)
(Ca1/Ce1) – N2	2.497(30)	(Ca2/Ce2) – N1	2.971(28)
(Ca1/Ce1) – N2	2.928(29)	(Ca2/Ce2) – N2	2.824(31)
(Ca1/Ce1) – N3	2.559(31)	(Ca2/Ce2) – N3	2.507(30)
(Ca1/Ce1) – N3	2.068(30)	(Ca2/Ce2) – N4	2.598(29)
(Ca1/Ce1) – N4	2.927(27)	(Ca2/Ce2) – N4	2.601(30)
		(Ca2/Ce2) – N4	2.965(29)

Current (mA)	CIE color coordinates	CRI	CCT (K)
100	(0.4012, 0.3527)	89.8	3243
200	(0.4003, 0.3515)	90.1	3254
300	(0.3993, 0.3504)	90.4	3268
400	(0.3975 <i>,</i> 0.3486)	90.7	3294
500	(0.3960, 0.3468)	90.9	3312
600	(0.3952 <i>,</i> 0.3459)	91.1	3322
700	(0.3937, 0.3438)	91.2	3341
800	(0.3927, 0.3423)	91.4	3351
900	(0.3919, 0.3413)	91.5	3360
1000	(0.3915, 0.3408)	91.5	3365

**Table S3.** CIE color coordinates, CRI and CCT of the fabricated white LED.

## **Notes and references**

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